



Silicon NPN Phototransistor, RoHS Compliant

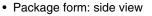


DESCRIPTION

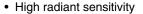
TEST2600 is a silicon NPN phototransistor with high radiant sensitivity in black, miniature, side view plastic package with daylight blocking filter. Filter bandwidth is matched with 900 nm to 950 nm IR emitters.

FEATURES

• Package type: leaded



• Dimensions (L x W x H in mm): 3.6 x 2.2 x 3.4



Daylight blocking filter matches with 940 nm emitters



- · Fast response times
- Angle of half sensitivity: $\phi_1 = \pm 30^{\circ}$, horizontal
- Package matches with IR emitter series TSSS2600
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

APPLICATIONS

- · Optical switches
- · Counters and sorters
- · Interrupters
- · Tape and card readers
- Encoders
- · Position sensors

| PRODUCT SUMMARY | | | |
|-----------------|----------------------|---------|-----------------------|
| COMPONENT | I _{ca} (mA) | φ (deg) | λ _{0.5} (nm) |
| TEST2600 | 2.5 | ± 30 | 850 to 980 |

Note

Test condition see table "Basic Characteristics"

| ORDERING INFORMAT | | | | |
|-------------------|-----------|------------------------------|--------------|--|
| ORDERING CODE | PACKAGING | REMARKS | PACKAGE FORM | |
| TEST2600 | Bulk | MOQ: 5000 pcs, 5000 pcs/bulk | Side view | |

Note

MOQ: minimum order quantity

| ABSOLUTE MAXIMUM RATINGS | | | | |
|-------------------------------------|--|-------------------|---------------|------|
| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT |
| Collector emitter voltage | | V _{CEO} | 70 | V |
| Emitter collector voltage | | V _{ECO} | 5 | V |
| Collector current | | Ic | 50 | mA |
| Collector peak current | $t_p/T = 0.5, t_p \le 10 \text{ ms}$ | I _{CM} | 100 | mA |
| Total power dissipation | T _{amb} ≤ 55 °C | P _V | 100 | mW |
| Junction temperature | | Tj | 100 | °C |
| Operating temperature range | | T _{amb} | - 40 to + 85 | °C |
| Storage temperature range | | T _{stg} | - 40 to + 100 | °C |
| Soldering temperature | $t \le 3$ s, 2 mm frpm case | T _{sd} | 260 | °C |
| Thermal resistance junction/ambient | Connected with Cu wire, 0.14 mm ² | R _{thJA} | 450 | K/W |

Note

T_{amb} = 25 °C, unless otherwise specified

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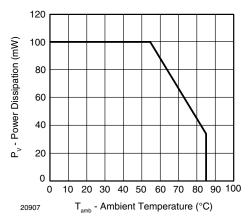


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS | | | | | | |
|--------------------------------------|---|----------------------|------|------------|------|------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| Collector emitter breakdown voltage | I _C = 1 mA | V _{(BR)CEO} | 70 | | | V |
| Collector emitter dark current | V _{CE} = 20 V, E = 0 | I _{CEO} | | 1 | 100 | nA |
| Collector emitter capacitance | V _{CE} = 5 V, f = 1 MHz, E = 0 | C _{CEO} | | 6 | | pF |
| Collector light current | $E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm},$ $V_{CE} = 5 \text{ V}$ | I _{ca} | 1 | 2.5 | | mA |
| Angle of half sensitivity | horizontal | Ψ1 | | ± 30 | | deg |
| | vertical | φ ₂ | | ± 60 | | deg |
| Wavelength of peak sensitivity | | λ_{p} | | 920 | | nm |
| Range of spectral bandwidth | | λ _{0.5} | | 850 to 980 | | nm |
| Collector emitter saturation voltage | $E_e = 1 \text{ mW/cm}^2, \ \lambda = 950 \text{ nm}, \ I_C = 0.1 \text{ mA}$ | V _{CEsat} | | | 0.3 | V |
| Turn-on time | $V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$ | t _{on} | | 6 | | μs |
| Turn-off time | $V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$ | t _{off} | | 5 | | μs |
| Cut-off frequency | $V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$ | f _c | | 110 | | kHz |

Note

 T_{amb} = 25 °C, unless otherwise specified

BASIC CHARACTERISTICS

 T_{amb} = 25 °C, unless otherwise specified

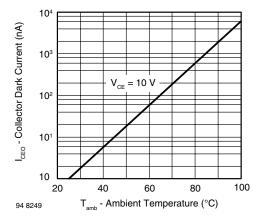


Fig. 2 - Collector Dark Current vs. Ambient Temperature

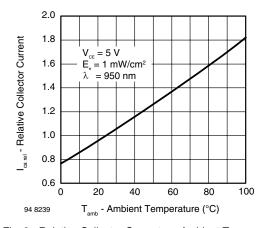


Fig. 3 - Relative Collector Current vs. Ambient Temperature



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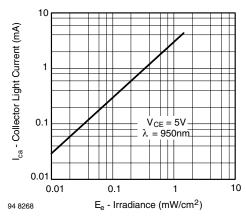


Fig. 4 - Collector Light Current vs. Irradiance

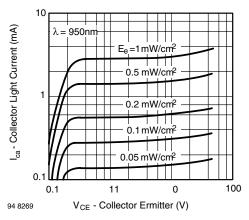


Fig. 5 - Collector Light Current vs. Collector Emitter Voltage

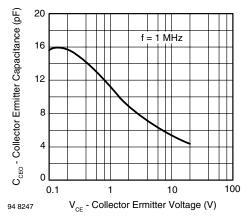


Fig. 6 - Collector Emitter Capacitance vs. Collector Emitter Voltage

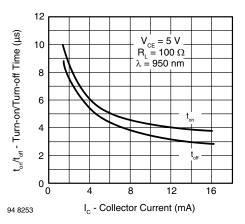


Fig. 7 - Turn-on/Turn-off Time vs. Collector Current

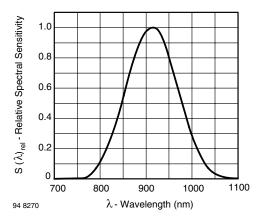


Fig. 8 - Relative Spectral Sensitivity vs. Wavelength

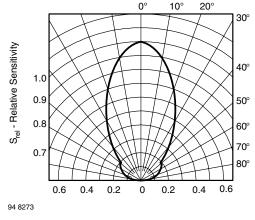


Fig. 9 - Relative Radiant Sensitivity vs. Angular Displacement

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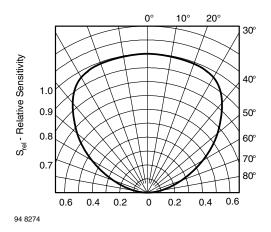
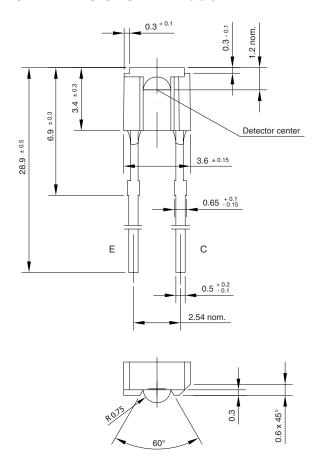
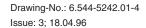


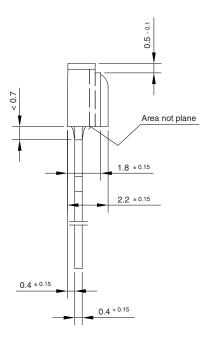
Fig. 10 - Relative Radiant Sensitivity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters





95 11487







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